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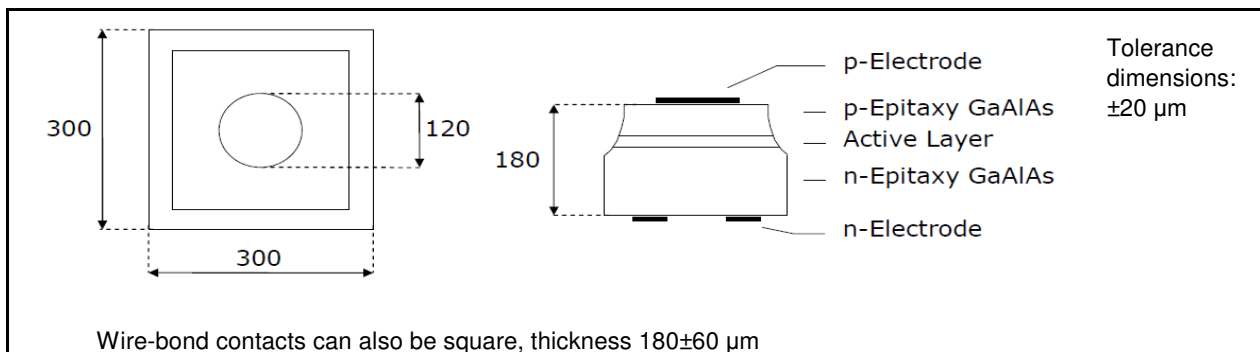
Data Sheet

LED Chip deep red

EOLC-660-14

Rev. 02, 2017

| Radiation | Type | Electrodes |
|-----------|-----------------|--------------|
| deep red | AlGaAs / AlGaAs | P (anode) up |



Optical and Electrical Characteristics

$T_{\text{amb}} = 25^\circ\text{C}$, unless otherwise specified

| Parameter | Test cond. | Symbol | Min | Typ | Max | Unit |
|--------------------|-----------------------|-----------------------|-----|--------|-----|---------------|
| Forward voltage | $I_F = 20 \text{ mA}$ | V_F | | 1.9 | 2.2 | V |
| Forward voltage | $I_F = 10 \text{ mA}$ | V_F | | 1.8 | 1.9 | V |
| Reverse current | $V_R = 5 \text{ V}$ | I_R | | | 10 | μA |
| Luminous intensity | $I_F = 10 \text{ mA}$ | I_v | 8 | 11 | | mcd |
| Luminous intensity | $I_F = 20 \text{ mA}$ | I_v | 16 | 22 | | mcd |
| Radiant power* | $I_F = 20 \text{ mA}$ | Φ_e | 1.3 | 1.8 | | mW |
| Peak wavelength | $I_F = 20 \text{ mA}$ | λ_p | 655 | 660 | 665 | nm |
| FWHM | $I_F = 20 \text{ mA}$ | $\Delta\lambda_{0.5}$ | | 23 | | nm |
| Switching times | $I_F = 20 \text{ mA}$ | t_r, t_f | | 80; 50 | | ns |

*Measured on bare chip on TO-18 header

All chips have got a burn-in in the non cut state for 2 sec at 50 mA

Packing

Chips on adhesive film with wire-bond side top

Art. No. 112 029



We reserve the right to make changes to improve technical design and may do so without further notice. Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer.